MT40G010N5

N-Channel Enhancement Mode Power MOSFET

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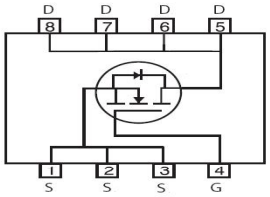
Feature Description

- 40V/245A

  $R_{DS(ON)}$= 0.9mΩ(typ.)@V_{GS} = 10V

- 100% Avalanche Tested
- Reliable and Rugged
- Halogen- Free Devices Available
- SGT MOSFET

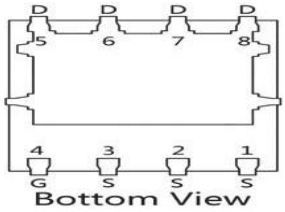
Simplified Schematic



Applications

- High Frequency Point-of-Load Synchronous Buck Converter
- Power Tool Application
- Networking DC-DC Power System

MARKING DIAGRAM & PIN ASSIGNMENT



Absolute Maximum Ratings (T_A = 25℃ unless otherwise noted)

Symbol	Parameter		Rating	Unit
Common Ratings (Tc=25°C Unless Otherwise Noted)				
V_{DSS}	Drain-Source Voltage		40	V
V_{GSS}	Gate-Source Voltage		±20	V
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to 150	°C
I_S	Source Current-Continuous(Body Diode)	Tc=25°C	168	A
Mounted on Large Heat Sink				
I_{DM}	Pulsed Drain Current *	Tc=25°C	656	A
I_D	Continuous Drain Current	Tc=25°C	245	A
		Tc=100°C	153	A
P_D	Maximum Power Dissipation	Tc=25°C	109	W
		Tc=100°C	38	W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		1.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient **		72	°C/W
E_{AS}	SinglePulsed-Avalanche Energy ***	L=0.3mH	480.2	mJ

Therma Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		1.3	℃/W

Electrical Characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=250μA	40			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=40V, V_{GS}=0V T_J=25℃			1	μA
		V_{DS}=40V, V_{GS}=0V T_J=125℃			100	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V, V_{DS}=0V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	1		4.0	V
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=20A		61		S
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=10V, I_D=20A T_J=25℃		0.9	1.6	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=20V,V_{GS}=0V, f=1.0MHz		3565		pF
C_{oss}	Output Capacitance			1712		pF
C_{rss}	Reverse Transfer Capacitance			108		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1.0MHz		1.9		Ω
Switching Parameters						
$t_{d(on)}$	Turn-on Delay Time	V_{GS}=10V, V_{DS}=20V, R_L=1Ω, R_{GEN}=3Ω		15.2		nS
t_r	Turn-on Rise Time			7.6		nS
$t_{d(off)}$	Turn-Off Delay Time			48.4		nS
t_f	Turn-Off Fall Time			13.6		nS
Q_g	Total Gate Charge	V_{GS}=10V, V_{DS}=20V, I_D=20A		53.8		nC
Q_{gs}	Gate-Source Charge			11		nC
Q_{gd}	Gate-Drain Charge			7.9		nC
Source-Drain Diode Characteristics						
I_{SD}	Source-Drain Current (Body Diode)				240	A
V_{SD}	Forward on Voltage (Note 3)	V_{GS}=0V, I_S=20A			1.2	V
t_{rr}	Reverse Recovery Time	I_F=20A, dI/dt=100A/μs		43.8		ns
Q_{rr}	Reverse Recovery Charge	I_F=20A, dI/dt=100A/μs		32.6		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.
Notes 2.E_{AS} condition: T_J=25℃,V_{DD}=40V,V_G=10V, Rg=25Ω, L=0.5mH.
Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.

Typical Operating Characteristics

Figure 1: Power Dissipation

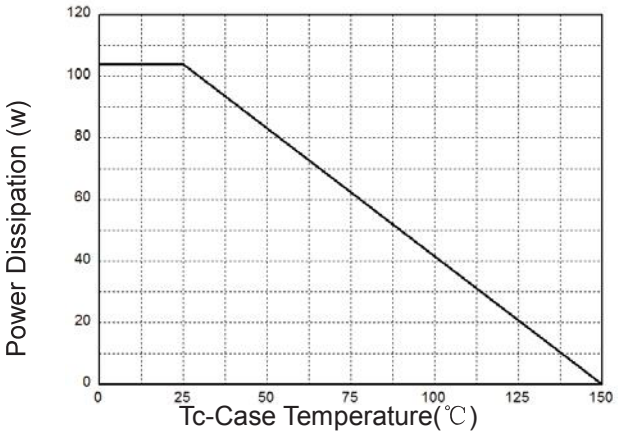


Figure 2: Drain Current

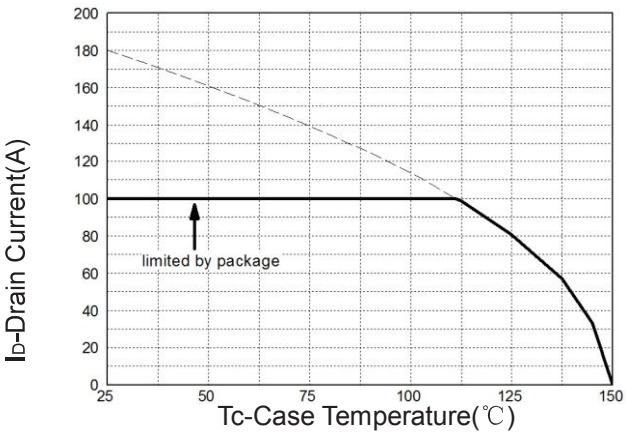


Figure 3: Safe Operation Area

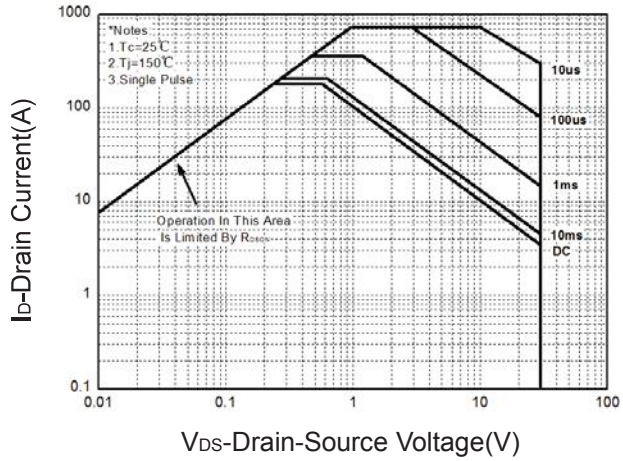


Figure 4: Thermal Transient Impedance

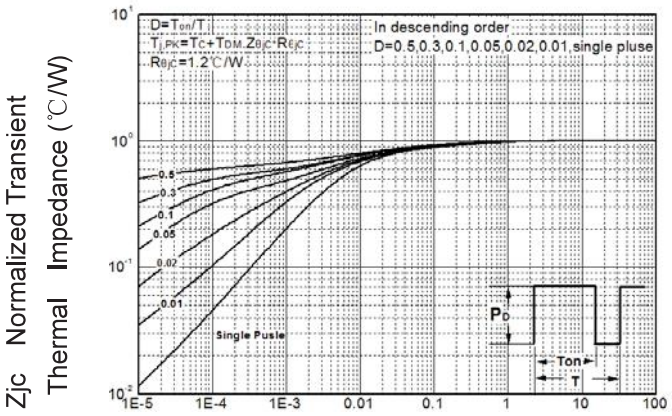


Figure 5: Output Characteristics

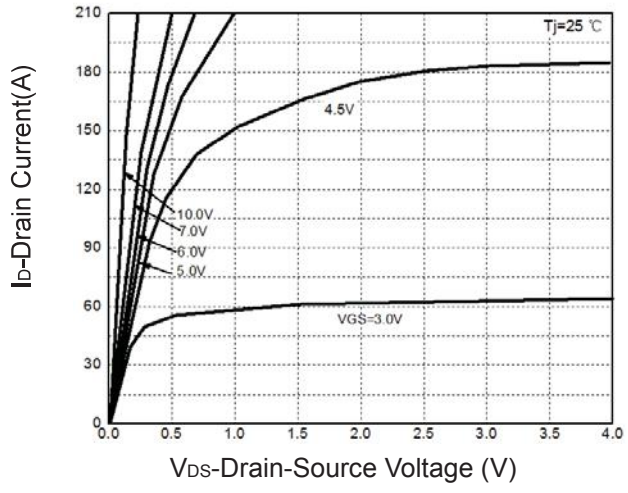
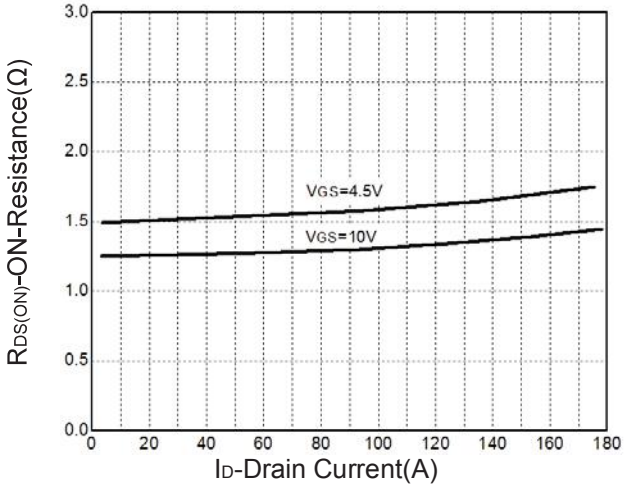


Figure 6: Drain-Source On Resistance



Typical Operating Characteristics(Cont.)

Figure 7: On-Resistance vs. Temperature

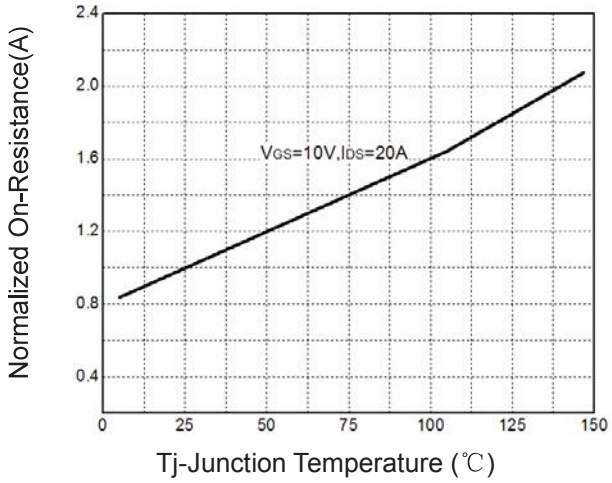


Figure 8: Source-Drain Diode Forward

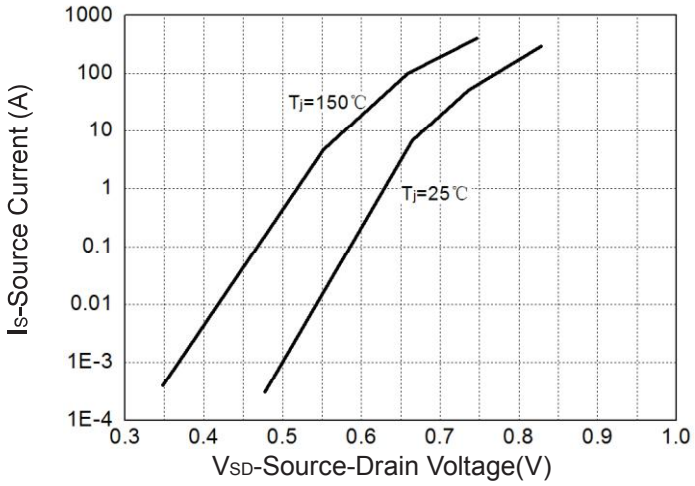


Figure 9: Capacitance Characteristics

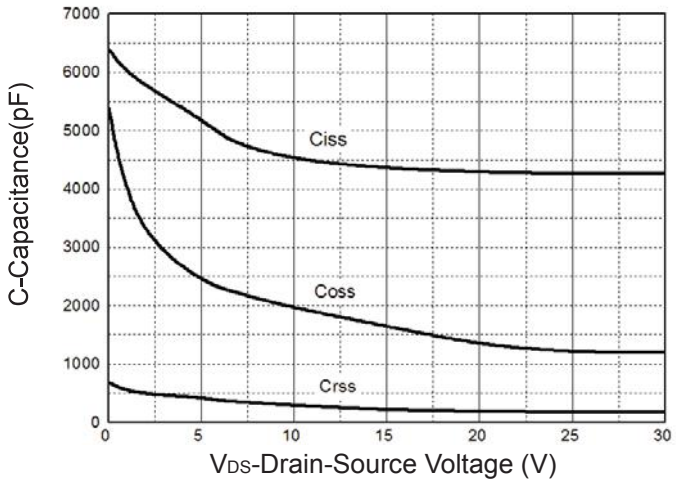
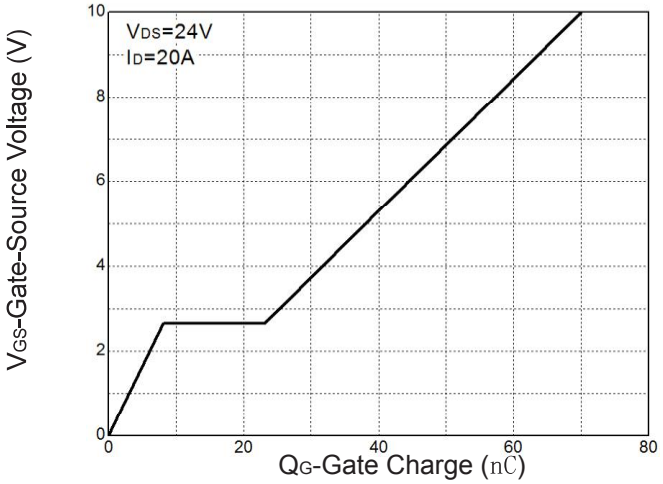
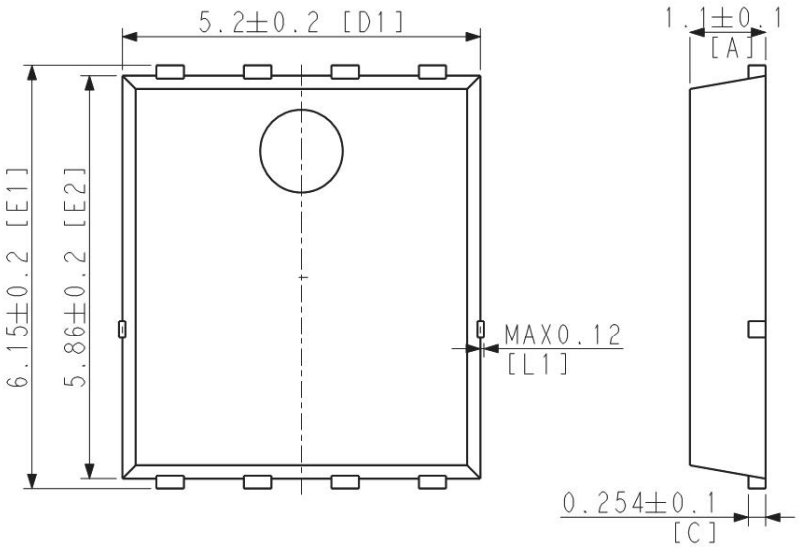


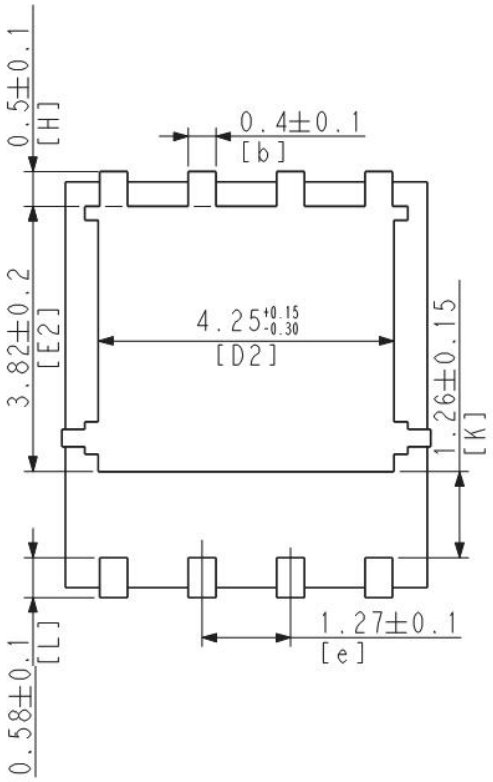
Figure 10: Gate Charge Characteristics



Package Information

PDFN5*6-8L





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